TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) Silicon NPN Epitaxial Type (PCT Process)

HN1B04F

Audio Frequency General Purpose Amplifier Applications
Driver Stage Amplifier Applications
Switching application

Q1:

Excellent h_{FE} linearity

: $h_{FE(2)}$ =25 (Min.) at V_{CE} = -6V I_{C} = -400mA

Q2:

Excellent h_{FE} linearity

: $h_{FE(2)} = 25$ (Min.) at $V_{CE} = 6V I_{C} = 400 \text{mA}$

Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-35	V
Collector-emitter voltage	V _{CEO}	-30	V
Emitter-base voltage	V _{EBO}	-5	٧
Collector current	I _C	-500	mA

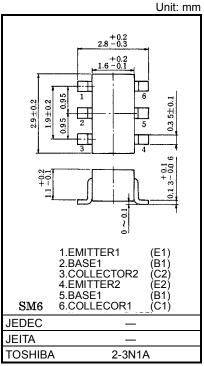
Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	35	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	Ic	500	mA

Q1,Q2 Common Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	300	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C

^{*} Total rating. 200mW per element must be exceeded.



Weight: 0.015g(typ.)

Q1 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = -35V$, $I_E = 0$	_	_	-100	nA
Emitter cut-off current	I _{EBO}	_	$V_{EB} = -5V, I_C = 0$	_	_	-100	nA
DC current gain	h _{FE(1)}	_	V _{CE} = -1V, I _C = -100mA	70	_	400	
	h _{FE(2)}	_	$V_{CE} = -6V, I_{C} = -400 \text{mA}$	25	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = -100mA, I _B = -10mA	_	-0.1	-0.25	V
Base-Emitter Voltage	V _{BE}	_	V _{CE} = -1V, I _C = -100mA	_	-0.8	-1.0	V
Transition frequency	f _T	_	$V_{CE} = -6V, I_{C} = -20mA$	_	200	_	MHz
Collector output capacitance	C _{ob}	_	$V_{CB} = -6V$, $I_E = 0$, $f = 1MHz$	_	7	_	pF

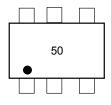
Q2 Electrical Characteristics (Ta = 25°C)

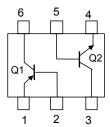
Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	V _{CB} = 35V, I _E = 0	_	_	100	nA
Emitter cut-off current	I _{EBO}	_	V _{EB} = 5V, I _C = 0	_	_	100	nA
DC current gain	h _{FE(1)}	_	V _{CE} = 1V, I _C = 100mA	70	_	400	
	h _{FE(2)}	_	V _{CE} = 6V, I _C = 400mA	25	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = 100mA, I _B = 10mA	_	0.1	0.25	V
Base-Emitter Voltage	V_{BE}	_	V _{CE} = 1V, I _C = 100mA	_	0.8	1.0	V
Transition frequency	f _T	_	V _{CE} = 6V, I _C = 20mA	_	300	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 6V, I _E = 0, f = 1MHz	_	7	_	pF

Marking

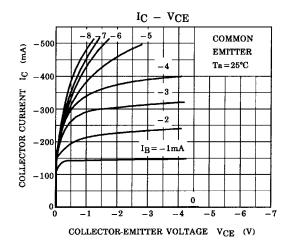
Equivalent Circuit (Top View)

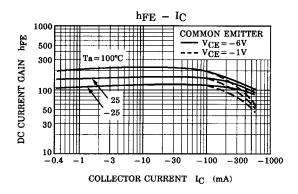
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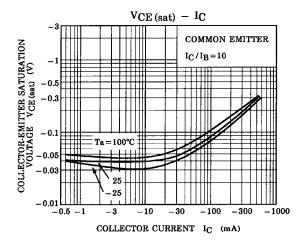


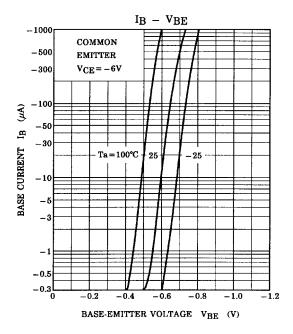


Q1 (PNP transistor)

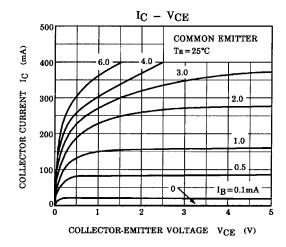


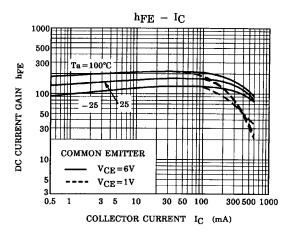


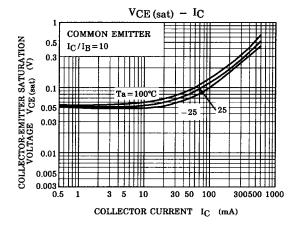


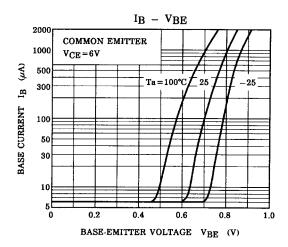


Q2 (NPN transistor)

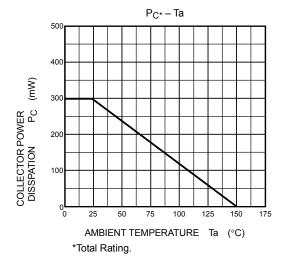








(Q1, Q2 Common)



5 2004-03-11

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Handbook" etc..

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6 2004-03-11